

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application.

**Listing of Claims:**

1-34. (previously canceled)

35. (currently amended) A method of fabricating a semiconductor structure, the method comprising the steps of:

- a. providing a semiconductor substrate;
- b. providing on said substrate a graded semiconductor region incorporating a first type of strain; and
- c. processing the graded region so as to introduce a second type of strain, the previously incorporated first type of strain reducing the process-induced second type of strain.

36-38. (previously canceled)

39. (previously amended) The method of claim 45, wherein the graded region comprises Si and Ge graded to an increasing concentration of Ge, and the step of incorporating compressive strain comprises decreasing a temperature at which the graded region is grown as the Ge concentration increases in the graded region.

40. (previously amended) The method of claim 39, wherein the step of incorporating compressive strain comprises growing alloys of  $\text{Ge}_x\text{Si}_{1-x}$  from  $x = 0$  to about  $x \approx 35\%$  at  $750^\circ\text{C}$ , growing alloys from  $x = 35$  to about  $x \approx 75\%$  at between  $650^\circ\text{C}$  and  $750^\circ\text{C}$ , and growing alloys greater than  $75\%$  at  $550^\circ\text{C}$ .

41-43. (previously canceled)

44. (previously amended) The method of claim 35, further comprising the step of planarizing at least one surface of the structure.

45. (previously added) The method of claim 35, wherein the first type of strain is compressive strain and the second type of strain is tensile strain.